

Figure 2. Atomic force microscopy images of GaN surfaces with different amounts of U-doping

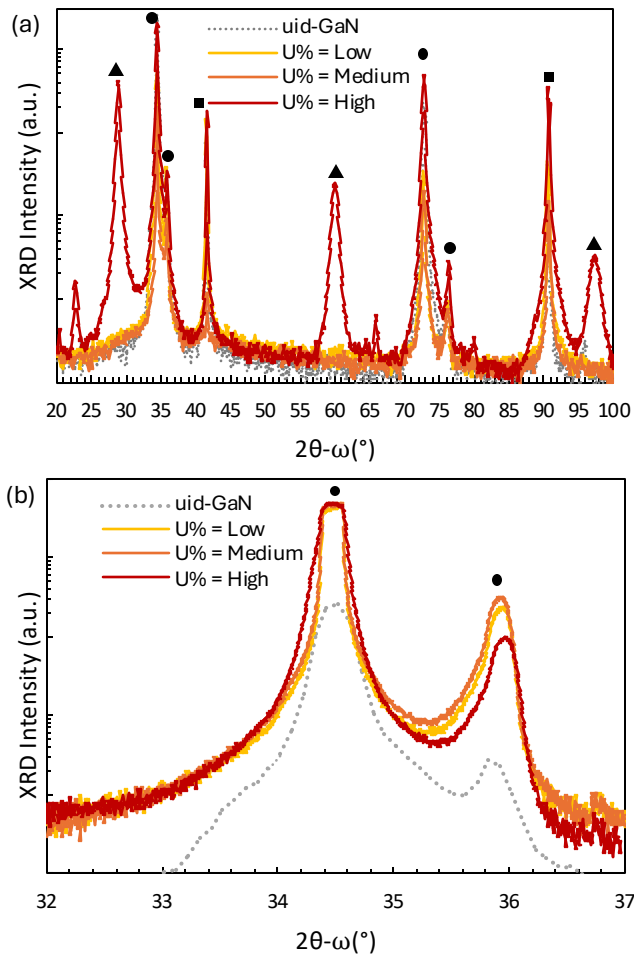


Figure 3.  $2\theta-\omega$  X-ray diffraction patterns of uid-GaN (grey, offset) and different levels of U-doping over a (a) wide angle and (b) the first order substrate peaks. Circles and squares indicate diffraction from the substrate. The precipitation of oriented material (stars) is observed with doping levels exceeding a certain amount.

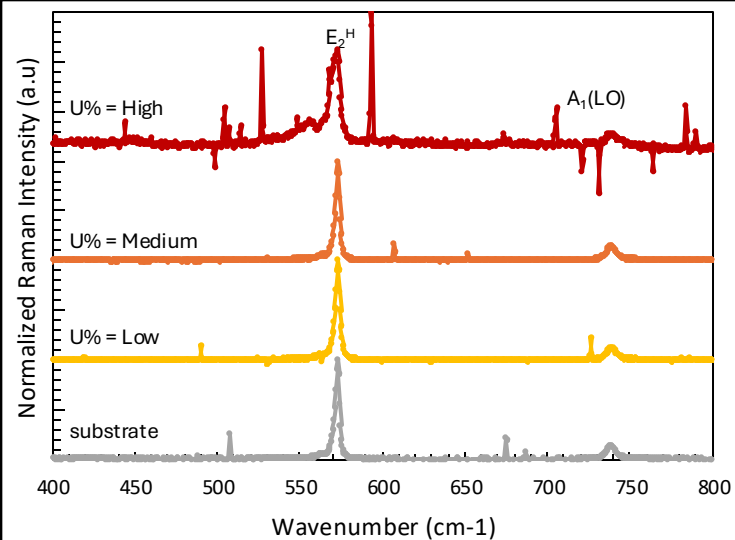


Figure 4. Raman spectroscopy of GaN with different amounts of U-doping